APPENDIX A

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Experimental Resours				
			Characteristics	
Concrete Experiments	Glass Substrate	Process Condition	Glass Compaction	V _{FB} *
		(Formation of SiO ₂ Film)	During Process	
No. 1				
Present Invention	Defined Claim 1	Temp: 450° C, Time: 30 min.	8 ~ 10 ppm	V _{FB} : 0 ~ 0.2V
-		(See page 11, lines 13 -)		
No. 2		Yamazaki (USP 6,025,630)		Impossible to fabricate
	←	Temp: 550° C, Time: 1 hr	About 60 ppm	devices
		(See col. 7, lines 14 -)		
No. 3		Abe (JP H8-195494)		
	←	Temp: 600° C, Time: 30 min.**	About 90 ppm	←
		(See col. 9, paragraph [0055]		
No. 4		Yamazaki (USP 6,025,630)		
	Annealed	Temp: 550° C, Time: 1 hr	About 6 ppm	V _{FB} : ~ 0V
		(See col. 7, line 14 -)		
2010/1 Lacatella				

^{*} V_{FB}: Flatband Voltage **Time is estimated using process temperature and thickness of oxide film